

KSB1116(A)

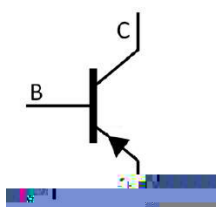
Rev.E Mar.-2016

KF \$0) GE G Silicon PNP transistor in a TO-92 Plastic Package.

BJ; (- (- ŽBž
Complementary pair with KSD1616(A).

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Audio frequency power amplifier, medium speed switching.



PIN1 Base PIN 2 Collector PIN 3 Emitter

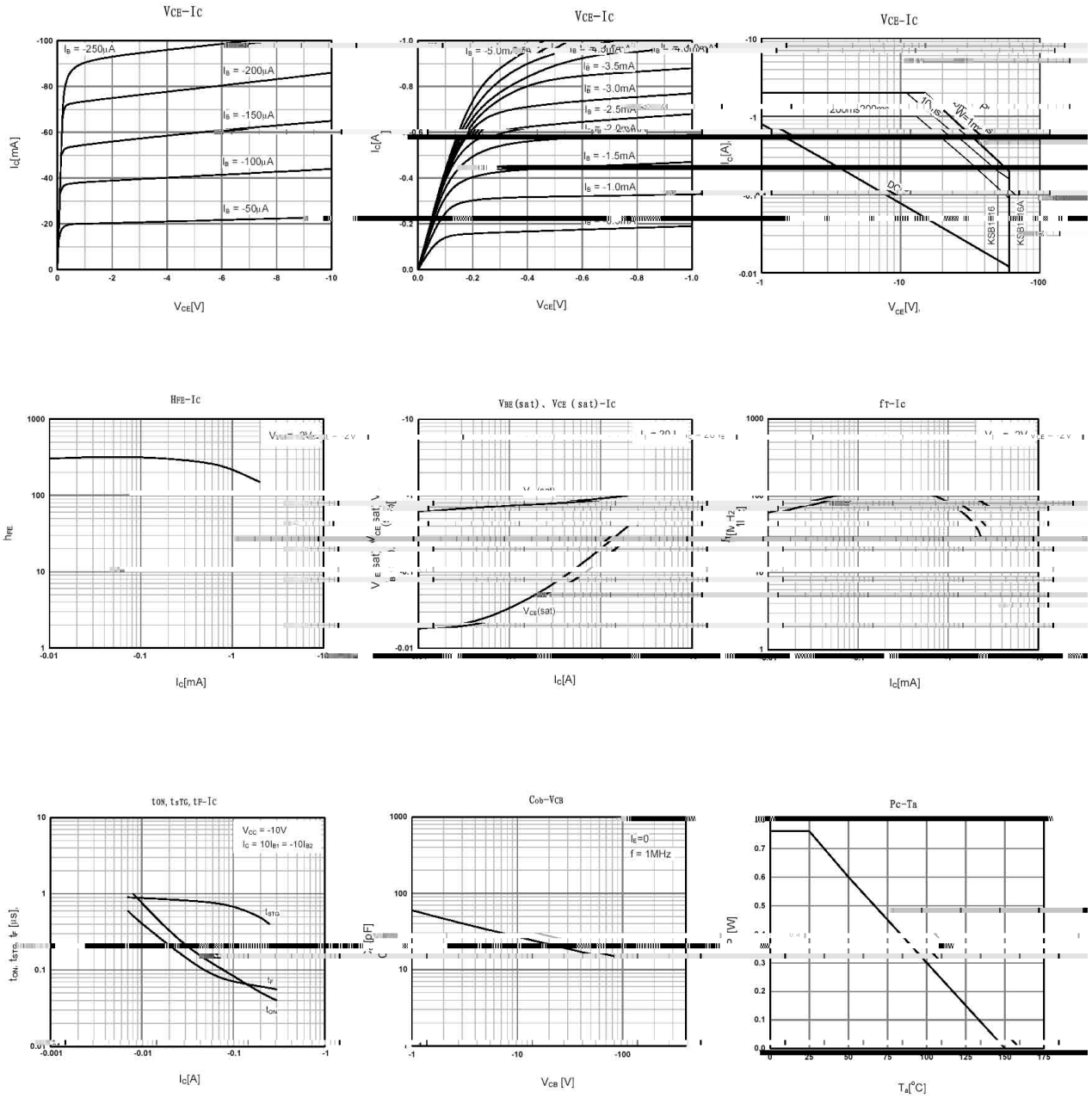
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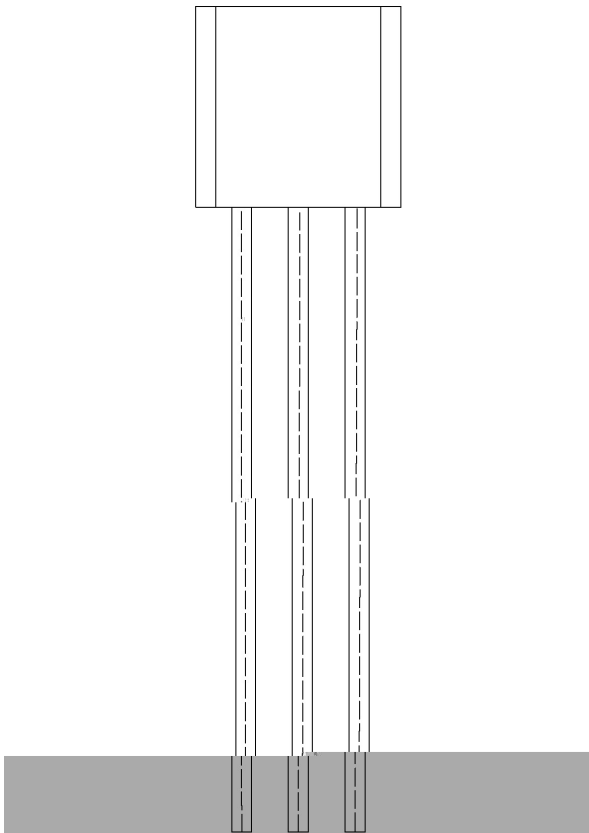
Parameter	Symbol		Rating	Unit
Collector to Base Voltage	V_{CBO}	KSB1116	-60	V
		KSB1116A	-120	
Collector to Emitter Voltage	V_{CEO}	KSB1116	-50	V
		KSB1116A	-60	
Emitter to Base Voltage	V_{EBO}		-6.0	V
Collector Current - Continuous	I_C		-1.0	A
Base Current – Continuous	I_B		-2.0	A
Collector Power Dissipation	P_C		750	mW
Junction Temperature	T_j		150	
Storage Temperature Range	T_{stg}		-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-60V$ $I_E=0$			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-6.0V$ $I_C=0$			-0.1	μA
DC Current Gain	$h_{FE(1)}$	KSB1116	135		600	
		$V_{CE}=-2.0V$ $I_C=-100mA$				

/ Electrical Characteristic Curve

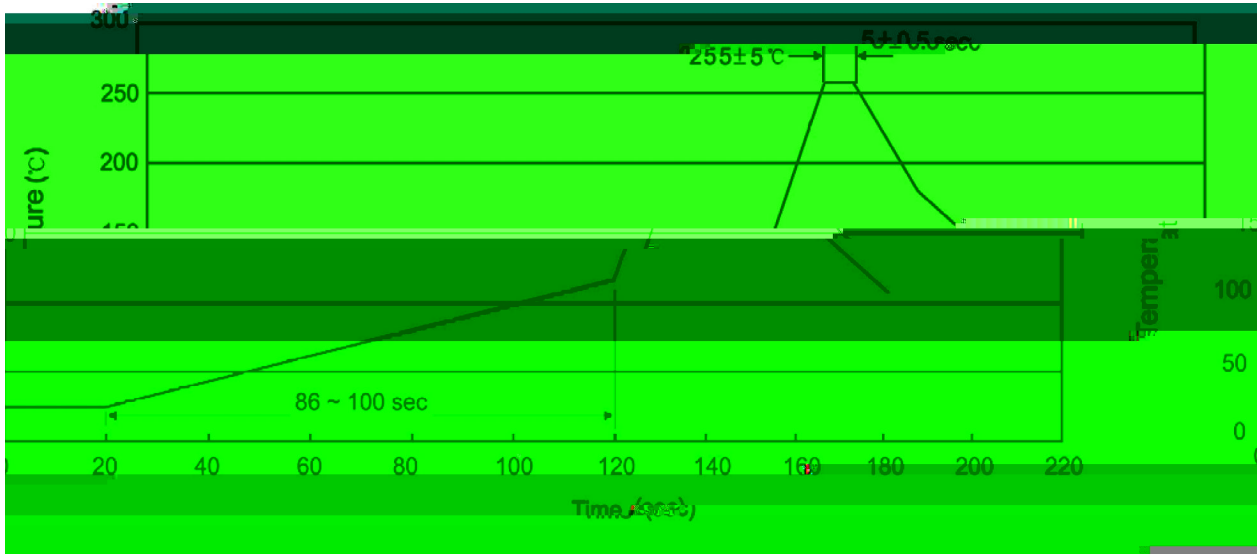


/ Marking Instructions



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() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|--------|-----|------------|----------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255..5 | | 5..0.5sec; | | 2.Peak Temp.:255..5 , Duration:5..0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270..5 10..1 sec. Temp:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type Units Dimension 314 0